

Si/SiC Hybrid Module – EliteSiC™, 3 Channel Flying Capacitor Boost 1000 V, 200 A IGBT, 1200 V, 60 A SiC Diode, Q2 Package

NXH600B100H4Q2F2S1G, SNXH600B100H4Q2F2S1G-S

The NXH600B100H4Q2S1G is a Si/SiC Hybrid three channel flying capacitor boost module. Each channel contains two 1000 V, 200 A IGBTs, and two 1200 V, 60 A SiC diodes. The module contains an NTC thermistor.

Features

- 3-channel Boost in Q2 Package
- Extremely Efficient Trench with Field Stop Technology
- Low Switching Loss Reduces System Power Dissipation
- Module Design Offers High Power Density
- Low Inductive Layout

Typical Applications

- Solar Inverters
- Uninterruptible Power Supplies Systems

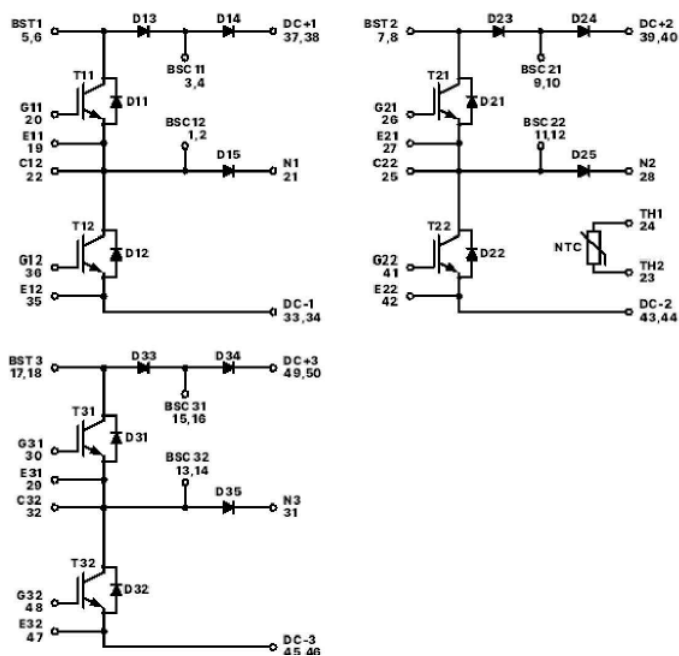
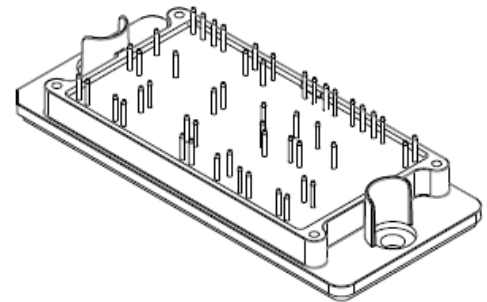
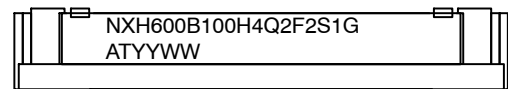


Figure 1. NXH600B100H4Q2F2S1G Schematic Diagram



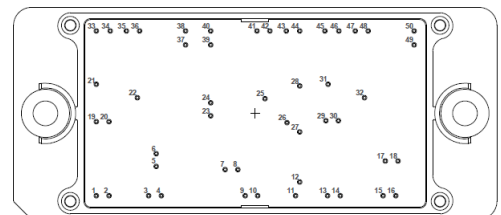
PIM56, 93x47 (SOLDER PIN)
CASE 180BK

MARKING DIAGRAM



NXH600B100H4Q2F2S1G = Specific Device Code
G = Pb-Free Package
AT = Assembly & Test Site Code
YYWW = Year and Work Week Code

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

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Table 1. ABSOLUTE MAXIMUM RATINGS (Note 1) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|-----------------------|----------|------------------|
| IGBT (T11, T12, T21, T22, T31, T32) | | | |
| Collector-Emitter Voltage | V_{CES} | 1000 | V |
| Gate-Emitter Voltage | V_{GE} | ± 20 | V |
| Positive Transient Gate-Emitter Voltage ($t_{\text{pulse}} = 5 \mu\text{s}$, $D < 0.10$) | | 30 | |
| Continuous Collector Current @ $T_C = 80^\circ\text{C}$ | I_C | 173 | A |
| Pulsed Peak Collector Current @ $T_C = 80^\circ\text{C}$ ($T_J = 175^\circ\text{C}$) | $I_{C(\text{Pulse})}$ | 519 | A |
| Maximum Power Dissipation ($T_J = 175^\circ\text{C}$) | P_{tot} | 422 | W |
| Minimum Junction Temperature | $T_{J\text{MIN}}$ | -40 | $^\circ\text{C}$ |
| Maximum Junction Temperature (Note 2) | $T_{J\text{MAX}}$ | 175 | $^\circ\text{C}$ |

IGBT INVERSE DIODE (D11, D12, D21, D22, D31, D32)

| | | | |
|---|-------------------|------|------------------|
| Peak Repetitive Reverse Voltage | V_{RRM} | 1200 | V |
| Continuous Forward Current @ $T_C = 80^\circ\text{C}$ | I_F | 66 | A |
| Repetitive Peak Forward Current ($T_J = 175^\circ\text{C}$) | I_{FRM} | 98 | A |
| Maximum Power Dissipation ($T_J = 175^\circ\text{C}$) | P_{tot} | 101 | W |
| Minimum Junction Temperature | $T_{J\text{MIN}}$ | -40 | $^\circ\text{C}$ |
| Maximum Junction Temperature | $T_{J\text{MAX}}$ | 175 | $^\circ\text{C}$ |

SILICON CARBIDE SCHOTTKY DIODE (D13, D14, D23, D24, D33, D34)

| | | | |
|---|-------------------|------|------------------|
| Peak Repetitive Reverse Voltage | V_{RRM} | 1200 | V |
| Continuous Forward Current @ $T_C = 80^\circ\text{C}$ | I_F | 63 | A |
| Repetitive Peak Forward Current ($T_J = 175^\circ\text{C}$) | I_{FRM} | 189 | A |
| Maximum Power Dissipation ($T_J = 175^\circ\text{C}$) | P_{tot} | 204 | W |
| Minimum Junction Temperature | $T_{J\text{MIN}}$ | -40 | $^\circ\text{C}$ |
| Maximum Junction Temperature | $T_{J\text{MAX}}$ | 175 | $^\circ\text{C}$ |

START-UP DIODE (D15, D25, D35)

| | | | |
|---|-------------------|------|------------------|
| Peak Repetitive Reverse Voltage | V_{RRM} | 1200 | V |
| Continuous Forward Current @ $T_C = 80^\circ\text{C}$ | I_F | 35 | A |
| Repetitive Peak Forward Current ($T_J = 175^\circ\text{C}$) | I_{FRM} | 105 | A |
| Maximum Power Dissipation ($T_J = 175^\circ\text{C}$) | P_{tot} | 84 | W |
| Minimum Junction Temperature | $T_{J\text{MIN}}$ | -40 | $^\circ\text{C}$ |
| Maximum Junction Temperature | $T_{J\text{MAX}}$ | 175 | $^\circ\text{C}$ |

THERMAL AND INSULATION PROPERTIES

THERMAL PROPERTIES

| | | | |
|---|------------------|------------|------------------|
| Operating Temperature under Switching Condition | T_{VJOP} | -40 to 150 | $^\circ\text{C}$ |
| Storage Temperature range | T_{stg} | -40 to 125 | $^\circ\text{C}$ |

INSULATION PROPERTIES

| | | | |
|---|-----------------|------|------------------|
| Isolation test voltage, $t = 1 \text{ sec}$, 50 Hz | V_{is} | 4000 | V_{RMS} |
| Creepage distance | | 12.7 | mm |
| Comparative tracking index | CTI | >600 | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.
2. Qualification at 175°C per discrete TO247.

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Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit |
|-----------|-----------------|--------|-----|-----|-----|------|
|-----------|-----------------|--------|-----|-----|-----|------|

IGBT (T11, T12, T21, T22, T31, T32) CHARACTERISTICS

| | | | | | | | |
|---------------------------------------|---|--|-------------|--------|---------|---------------|---------------|
| Collector-Emitter Breakdown Voltage | $V_{GE} = 0\text{ V}, I_C = 2\text{ mA}$ | $V_{(BR)CES}$ | 1000 | 1150 | - | V | |
| Collector-Emitter Cutoff Current | $V_{GE} = 0\text{ V}, V_{CE} = 1000\text{ V}$ | I_{CES} | - | - | 20 | μA | |
| Collector-Emitter Saturation Voltage | $V_{GE} = 15\text{ V}, I_C = 200\text{ A}, T_J = 25^\circ\text{C}$ | $V_{CE(sat)}$ | - | 1.88 | 2.3 | V | |
| | $V_{GE} = 15\text{ V}, I_C = 200\text{ A}, T_J = 150^\circ\text{C}$ | | - | 2.4 | - | | |
| Gate-Emitter Threshold Voltage | $V_{GE} = V_{CE}, I_C = 200\text{ mA}$ | $V_{GE(TH)}$ | 4 | 4.98 | 6 | V | |
| Gate Leakage Current | $V_{GE} = \pm 20\text{ V}, V_{CE} = 0\text{ V}$ | I_{GES} | - | - | 350 | nA | |
| Internal Gate Resistor | | r_G | - | 3 | - | Ω | |
| Turn-on Delay Time | $T_J = 25^\circ\text{C}$ $V_{CE} = 600\text{ V}, I_C = 50\text{ A}$ $V_{GE} = -9\text{ V}, 15\text{ V}, R_{Gon} = 9\ \Omega, R_{Goff} = 25\ \Omega$ | $t_{d(on)}$ | - | 119.75 | - | ns | |
| Rise Time | | t_r | - | 30.08 | - | | |
| Turn-off Delay Time | | $t_{d(off)}$ | - | 614.57 | - | | |
| Fall Time | | t_f | - | 26.85 | - | | |
| Turn-on Switching Loss per Pulse | | E_{on} | - | 860 | - | | μJ |
| Turn off Switching Loss per Pulse | | E_{off} | - | 1500 | - | | |
| Turn-on Delay Time | | $T_J = 125^\circ\text{C}$ $V_{CE} = 600\text{ V}, I_C = 50\text{ A}$ $V_{GE} = -9\text{ V}, 15\text{ V}, R_{Gon} = 9\ \Omega, R_{Goff} = 25\ \Omega$ | $t_{d(on)}$ | - | 119.97 | | - |
| Rise Time | t_r | | - | 32.09 | - | | |
| Turn-off Delay Time | $t_{d(off)}$ | | - | 706.72 | - | | |
| Fall Time | t_f | | - | 40.22 | - | | |
| Turn-on Switching Loss per Pulse | E_{on} | | - | 1120 | - | μJ | |
| Turn off Switching Loss per Pulse | E_{off} | | - | 2750 | - | | |
| Input Capacitance | $V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | | C_{ies} | - | 12687.7 | - | pF |
| Output Capacitance | | C_{oes} | - | 418.0 | - | | |
| Reverse Transfer Capacitance | | C_{res} | - | 73.9 | - | | |
| Total Gate Charge | $V_{CE} = 600\text{ V}, I_C = 40\text{ A}, V_{GE} = -15\text{ V} \sim 15\text{ V}$ | Q_g | - | 680 | - | nC | |
| Thermal Resistance – chip-to-heatsink | Thermal grease, Thickness = 2.1 Mil $\pm 2\%$, $\lambda = 2.87\text{ W/mK}$ | R_{thJH} | - | 0.420 | - | K/W | |
| Thermal Resistance – chip-to-case | | R_{thJC} | - | 0.225 | - | K/W | |

IGBT INVERSE DIODE (D11, D12, D21, D22, D31, D32) CHARACTERISTICS

| | | | | | | |
|---------------------------------------|---|------------|---|-------|-----|-----|
| Diode Forward Voltage | $I_F = 50\text{ A}, T_J = 25^\circ\text{C}$ | V_F | - | 1.15 | 1.5 | V |
| | $I_F = 50\text{ A}, T_J = 175^\circ\text{C}$ | | - | 1.08 | - | |
| Thermal Resistance – chip-to-heatsink | Thermal grease, Thickness = 2.1 Mil $\pm 2\%$, $\lambda = 2.87\text{ W/mK}$ | R_{thJH} | - | 0.956 | - | K/W |
| Thermal Resistance – chip-to-case | | R_{thJC} | - | 0.800 | - | K/W |

DIODES (D13, D14, D23, D24, D33, D34) CHARACTERISTICS

| | | | | | | |
|---------------------------------------|--|-----------|---|---------|-----|------------------|
| Diode Forward Voltage | $I_F = 60\text{ A}, T_J = 25^\circ\text{C}$ | V_F | - | 1.51 | 2.2 | V |
| | $I_F = 60\text{ A}, T_J = 175^\circ\text{C}$ | | - | 2.14 | - | |
| Reverse Recovery Time | $T_J = 25^\circ\text{C}$ $V_{CE} = 600\text{ V}, I_C = 50\text{ A}$ $V_{GE} = -9\text{ V}, 15\text{ V}, R_{Gon} = 9\ \Omega$ | t_{rr} | - | 28.14 | - | ns |
| Reverse Recovery Charge | | Q_{rr} | - | 304.98 | - | nC |
| Peak Reverse Recovery Current | | I_{RRM} | - | 18.8 | - | A |
| Peak Rate of Fall of Recovery Current | | di/dt | - | 1389.12 | - | A/ μs |
| Reverse Recovery Energy | | E_{rr} | - | 105.08 | - | μJ |
| | | | - | - | - | |

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Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit |
|-----------|-----------------|--------|-----|-----|-----|------|
|-----------|-----------------|--------|-----|-----|-----|------|

DIODES (D13, D14, D23, D24, D33, D34) CHARACTERISTICS

| | | | | | | |
|---------------------------------------|---|------------|---|--------|---|------------------|
| Reverse Recovery Time | $T_J = 125^\circ\text{C}$ $V_{CE} = 600\text{ V}, I_C = 50\text{ A}$ $V_{GE} = -9\text{ V}, 15\text{ V}, R_{Gon} = 9\ \Omega$ | t_{rr} | – | 45.73 | – | ns |
| Reverse Recovery Charge | | Q_{rr} | – | 583.95 | – | nC |
| Peak Reverse Recovery Current | | I_{RRM} | – | 24.08 | – | A |
| Peak Rate of Fall of Recovery Current | | di/dt | – | 1236 | – | A/ μs |
| Reverse Recovery Energy | | E_{rr} | – | 216.04 | – | μJ |
| Thermal Resistance – chip-to-heatsink | Thermal grease, Thickness = 2.1 Mil $\pm 2\%$, $\lambda = 2.87\text{ W/mK}$ | R_{thJH} | – | 0.599 | – | K/W |
| Thermal Resistance – chip-to-case | | R_{thJC} | – | 0.466 | – | K/W |

START-UP DIODE (D15, D25, D35) CHARACTERISTICS

| | | | | | | |
|---------------------------------------|---|------------|---|-------|-----|-----|
| Diode Forward Voltage | $I_F = 30\text{ A}, T_J = 25^\circ\text{C}$ | V_F | – | 2.25 | 3.2 | V |
| | $I_F = 30\text{ A}, T_J = 175^\circ\text{C}$ | | – | 1.8 | – | |
| Thermal Resistance – chip-to-heatsink | Thermal grease, Thickness = 2.1 Mil $\pm 2\%$, $\lambda = 2.87\text{ W/mK}$ | R_{thJH} | – | 1.309 | – | K/W |
| Thermal Resistance – chip-to-case | | R_{thJC} | – | 1.133 | – | K/W |

THERMISTOR CHARACTERISTICS

| | | | | | | |
|----------------------------|----------------------------------|--------------|----|-------|---|------------|
| Nominal resistance | $T = 25^\circ\text{C}$ | R_{25} | – | 5 | – | k Ω |
| Nominal resistance | $T = 100^\circ\text{C}$ | R_{100} | – | 490.6 | – | Ω |
| Deviation of R25 | | $\Delta R/R$ | –1 | – | 1 | % |
| Power dissipation | | P_D | – | 5 | – | mW |
| Power dissipation constant | | | – | 1.3 | – | mW/K |
| B-value | $B(25/85)$, tolerance $\pm 1\%$ | | – | 3435 | – | K |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

| Orderable Part Number | Marking | Package | Shipping |
|------------------------|------------------------|--|-------------------------|
| NXH600B100H4Q2F2S1G | NXH600B100H4Q2F2S1G | Q2BOOST, Case 180BK (Pb-Free and Halide-Free Solder Pins) | 12 Units / Blister Tray |
| SNXH600B100H4Q2F2S1G-S | SNXH600B100H4Q2F2S1G-S | Q2BOOST, Case 180BK (Pb-Free and Halide-Free Solder Pins) | 12 Units / Blister Tray |

NXH600B100H4Q2F2S1G, SNXH600B100H4Q2F2S1G-S

TYPICAL CHARACTERISTICS - T11||D13, T12||D14, T21||D23, T22||D24, T31||D33, T32||D34

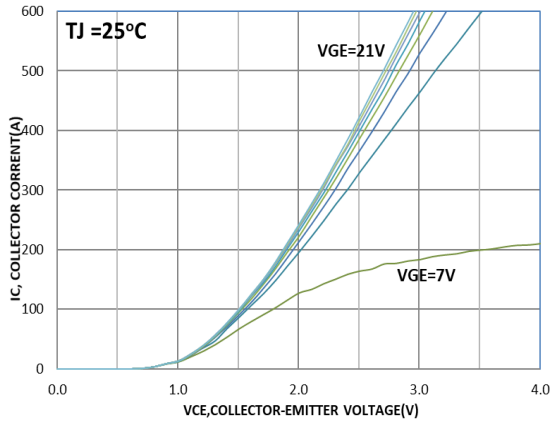


Figure 2. Typical Output Characteristics

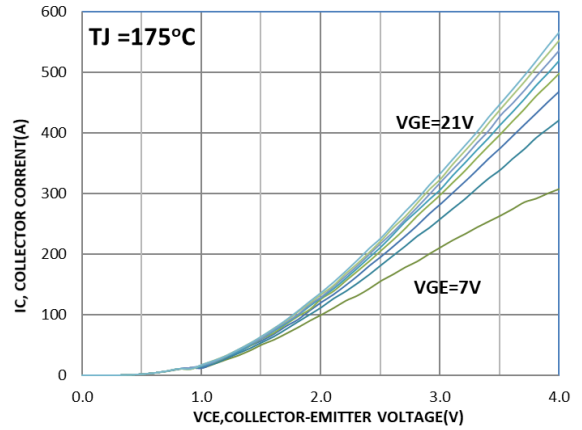


Figure 3. Typical Output Characteristics

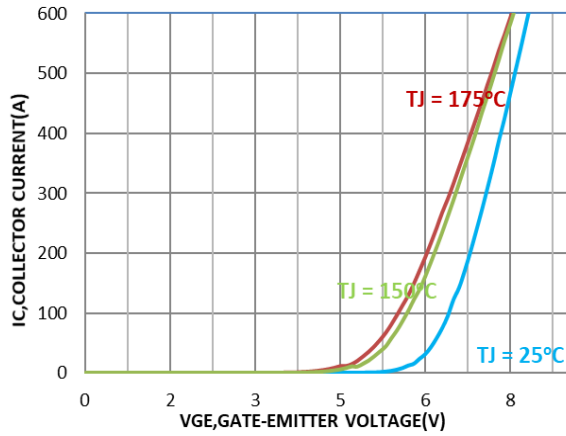


Figure 4. Transfer Characteristics

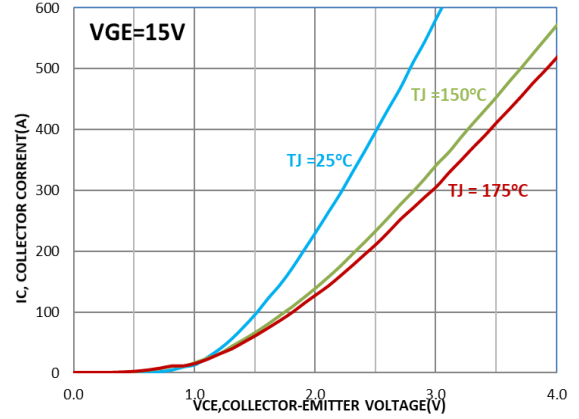


Figure 5. Saturation Voltage Characteristic

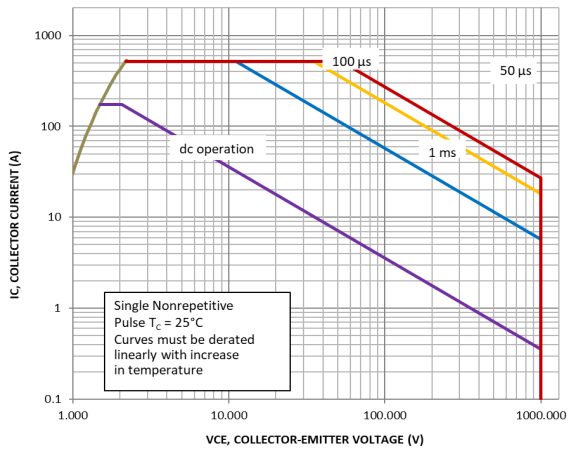


Figure 6. FBSOA

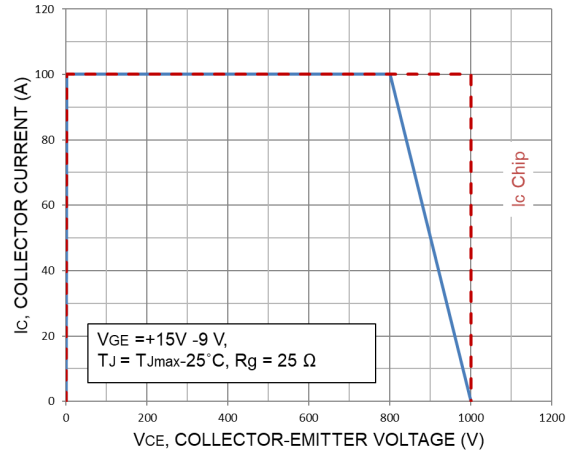


Figure 7. RBSOA

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TYPICAL CHARACTERISTICS – T11||D13, T12||D14, T21||D23, T22||D24, T31||D33, T32||D34 (CONTINUED)

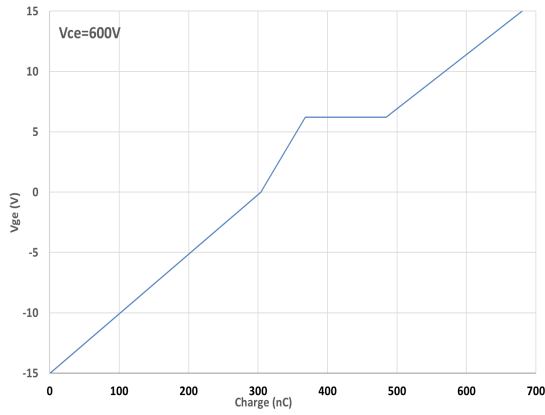


Figure 8. Gate Voltage vs. Gate Charge

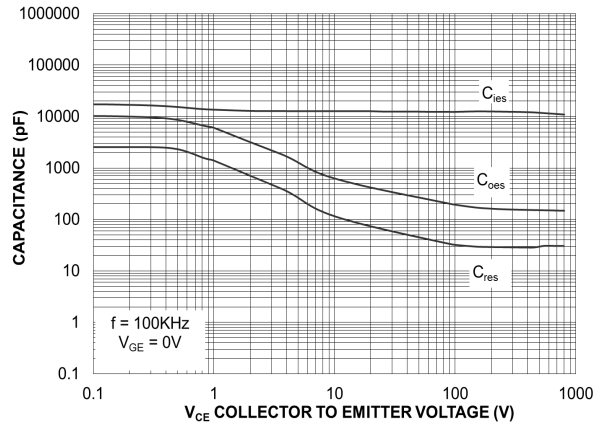


Figure 9. Capacitance

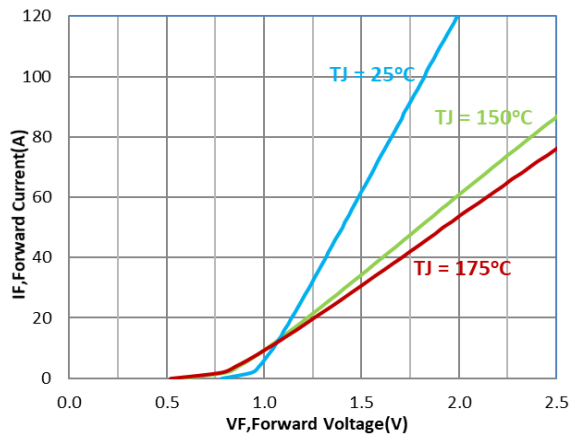


Figure 10. Diode Forward Characteristics

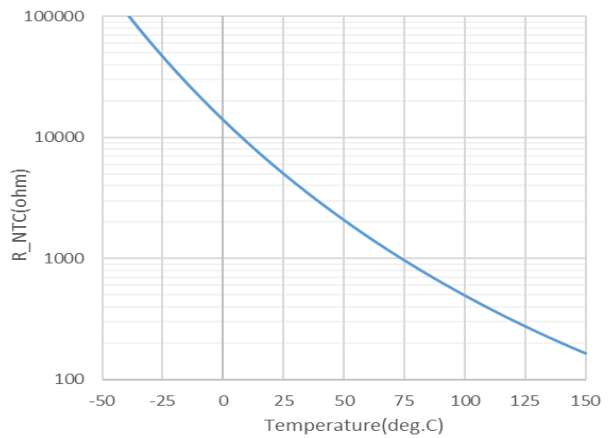


Figure 11. Temperature vs. NTC Value

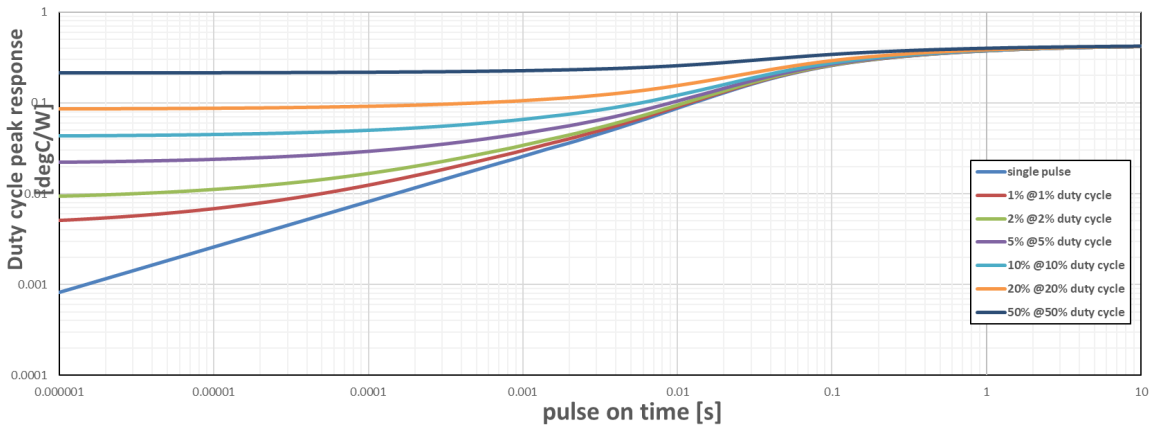


Figure 12. Transient Thermal Impedance (IGBT Rthjc)

NXH600B100H4Q2F2S1G, SNXH600B100H4Q2F2S1G-S

TYPICAL CHARACTERISTICS – T11||D13, T12||D14, T21||D23, T22||D24, T31||D33, T32||D34 (CONTINUED)

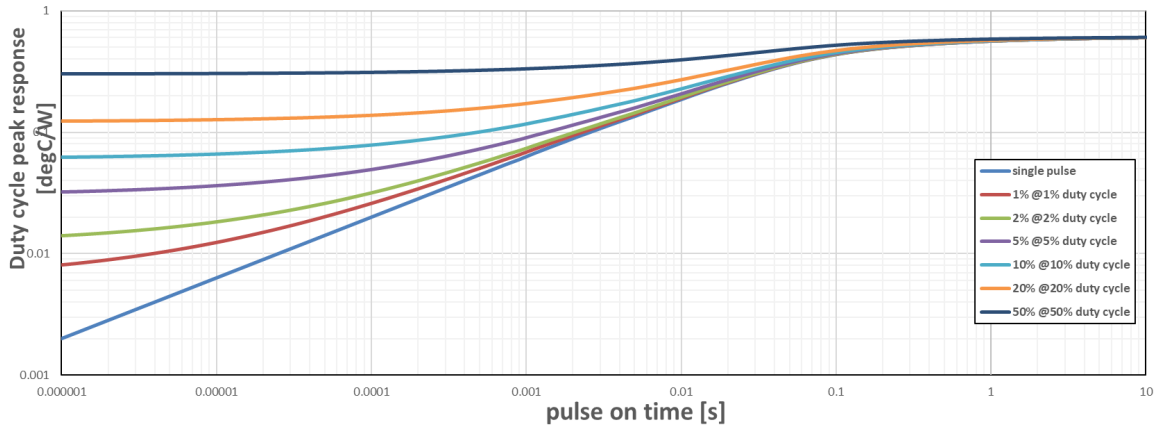


Figure 13. Transient Thermal Impedance (DIODE Rthjc)

TYPICAL CHARACTERISTICS – D11, D12, D21, D22, D31, D32 DIODE

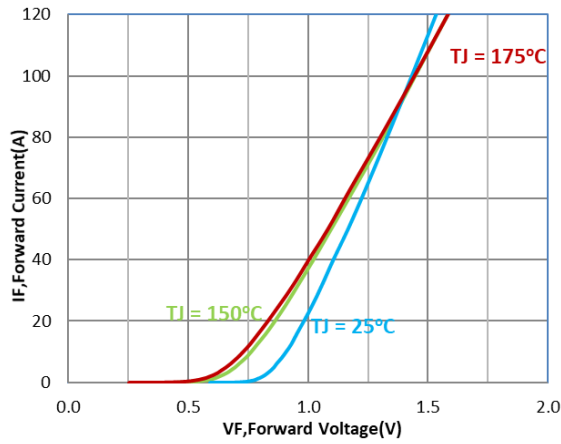


Figure 14. Diode Forward Characteristics

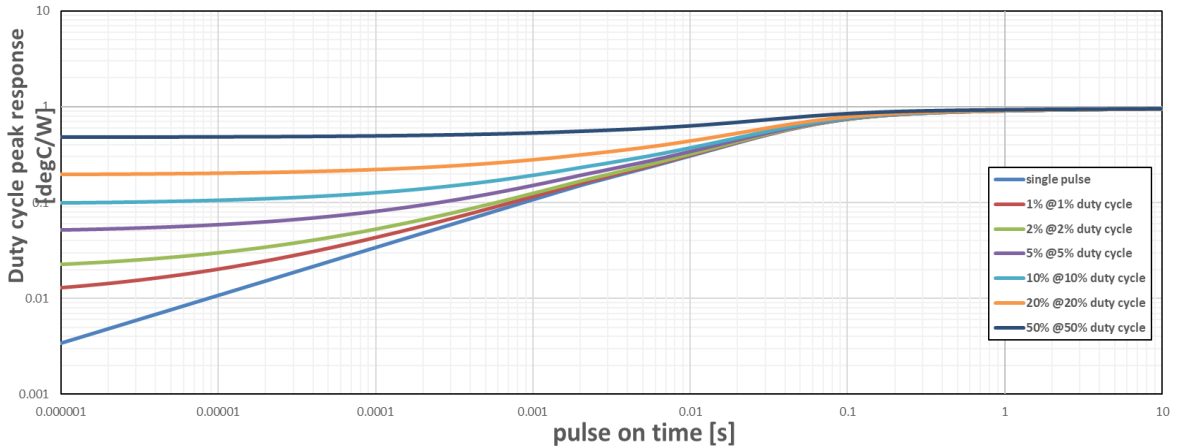


Figure 15. Transient Thermal Impedance (Rthjc)

NXH600B100H4Q2F2S1G, SNXH600B100H4Q2F2S1G-S

TYPICAL CHARACTERISTICS – D15, D25, D35 DIODE

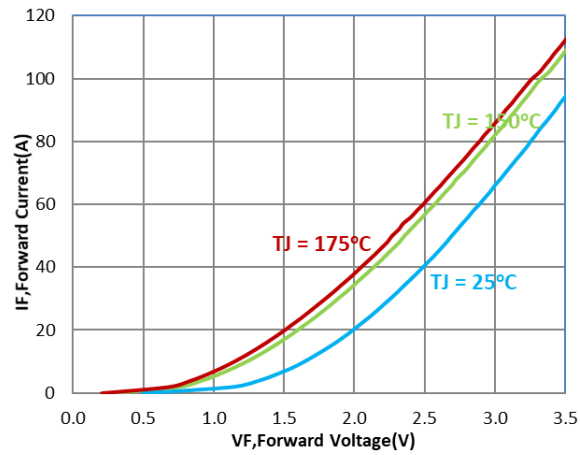


Figure 16. Diode Forward Characteristics

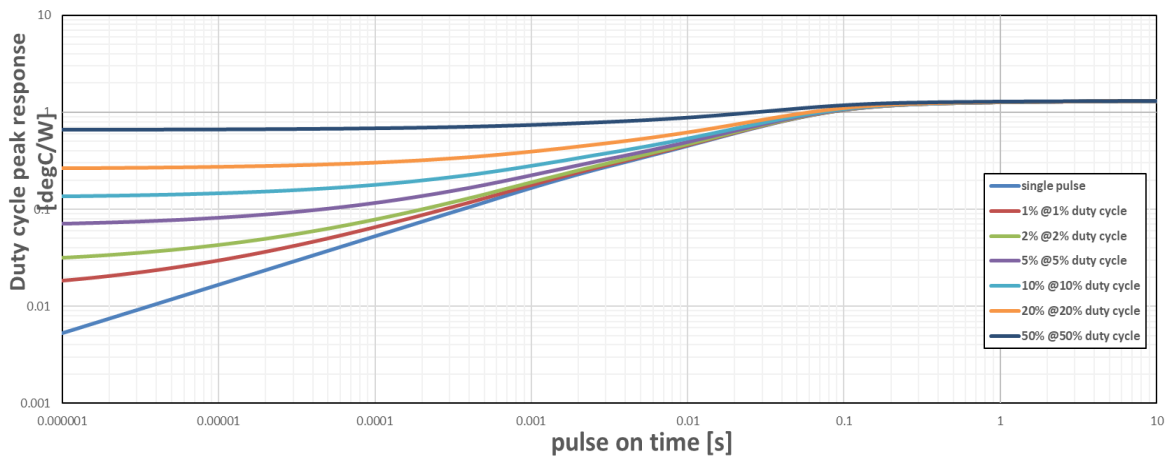


Figure 17. Transient Thermal Impedance (Rthjc)

NXH600B100H4Q2F2S1G, SNXH600B100H4Q2F2S1G-S

TYPICAL CHARACTERISTICS – T11||D13, T12||D14, T21||D23, T22||D24, T31||D33, T32||D34

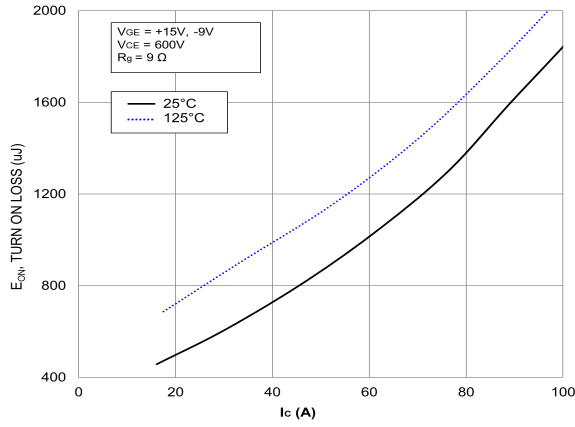


Figure 18. Typical Turn On Loss vs. I_C

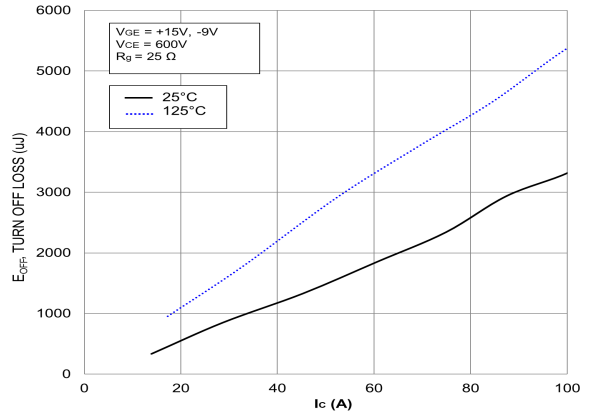


Figure 19. Typical Turn Off Loss vs. I_C

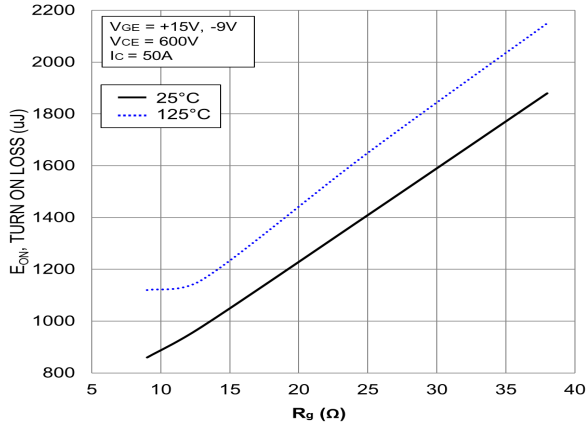


Figure 20. Typical Turn On Loss vs. R_G

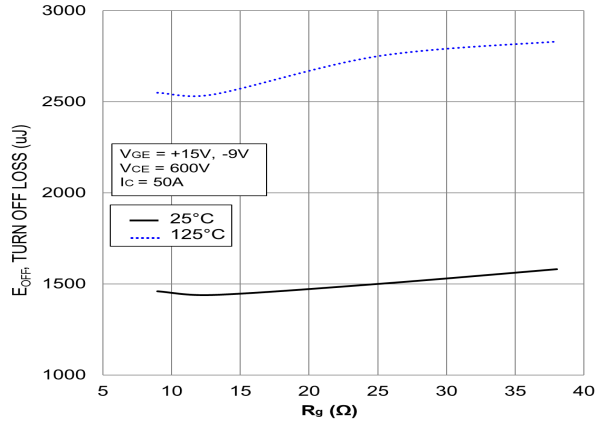


Figure 21. Typical Turn Off Loss vs. R_G

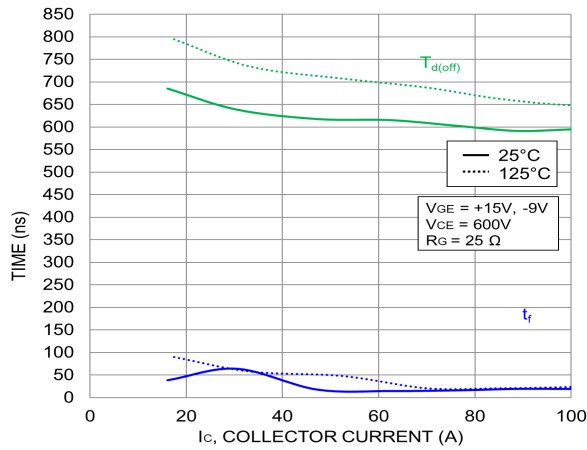


Figure 22. Typical Turn-Off Switching Time vs. I_C

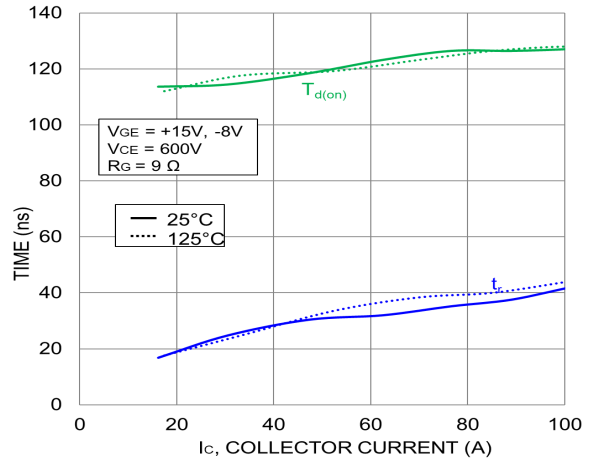


Figure 23. Typical Turn-On Switching Time vs. I_C

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TYPICAL CHARACTERISTICS – T11||D13, T12||D14, T21||D23, T22||D24, T31||D33, T32||D34 (continued)

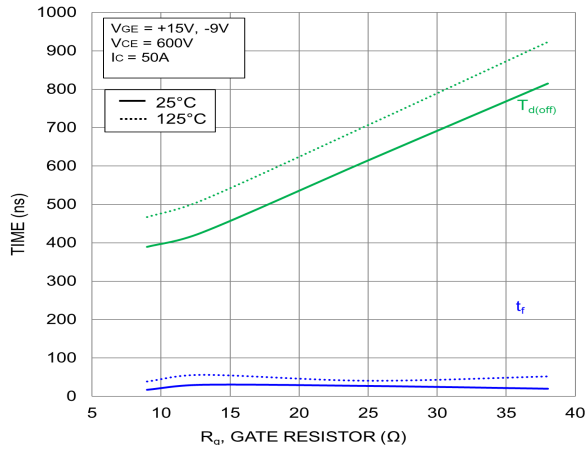


Figure 24. Typical Turn-Off Switching Time vs. R_g

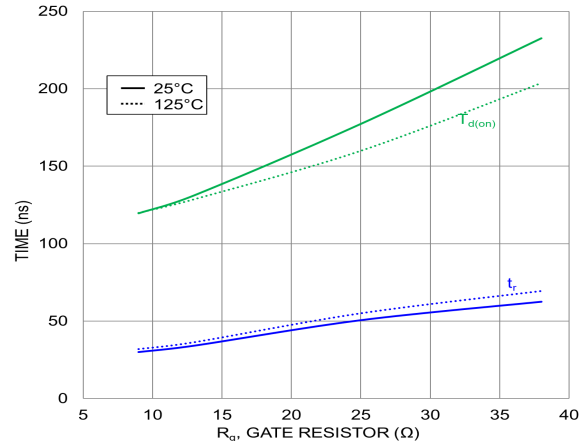


Figure 25. Typical Turn-On Switching Time vs. R_g

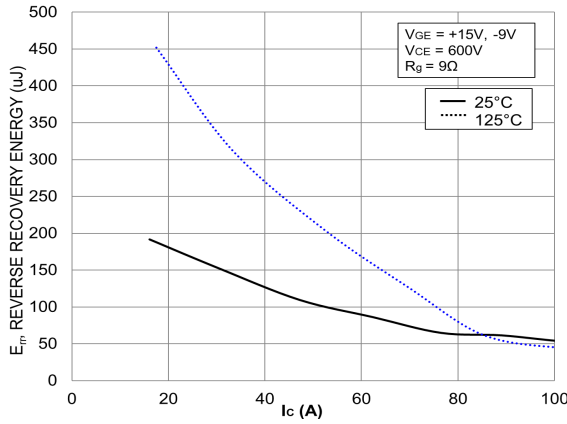


Figure 26. Typical Reverse Recovery Energy Loss vs. I_C

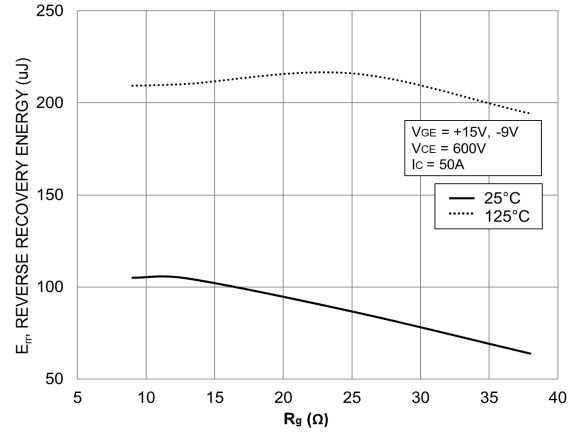


Figure 27. Typical Reverse Recovery Energy Loss vs. R_g

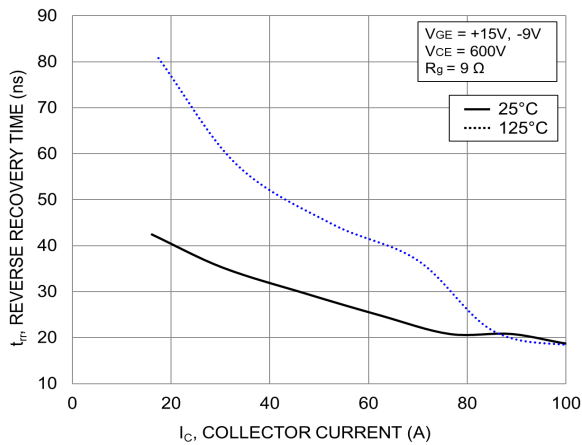


Figure 28. Typical Reverse Recovery Time vs. I_C

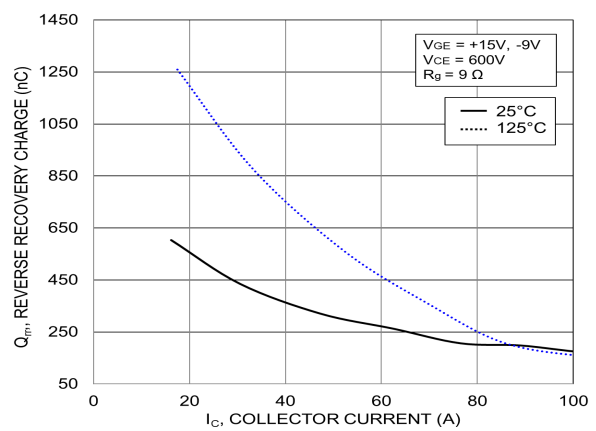


Figure 29. Typical Reverse Recovery Charge vs. I_C

NXH600B100H4Q2F2S1G, SNXH600B100H4Q2F2S1G-S

TYPICAL CHARACTERISTICS – T11||D13, T12||D14, T21||D23, T22||D24, T31||D33, T32||D34 (continued)

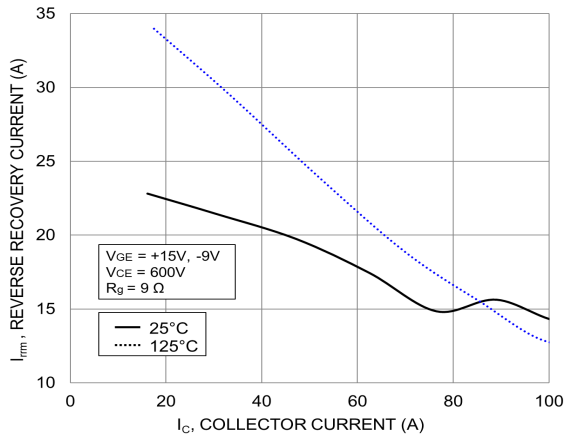


Figure 30. Typical Reverse Recovery Current vs. I_C

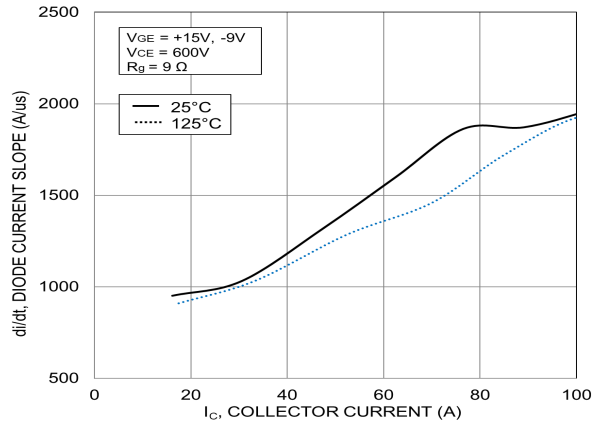


Figure 31. Typical di/dt vs. I_C

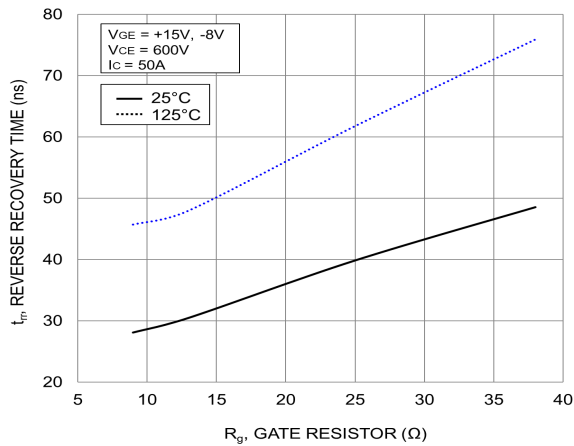


Figure 32. Typical Reverse Recovery Time vs. R_g

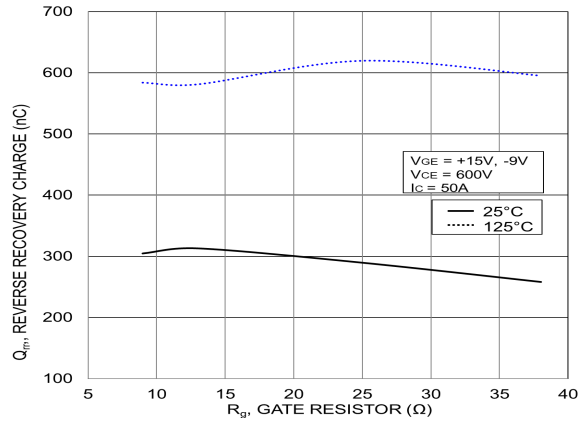


Figure 33. Typical Reverse Recovery Charge vs. R_g

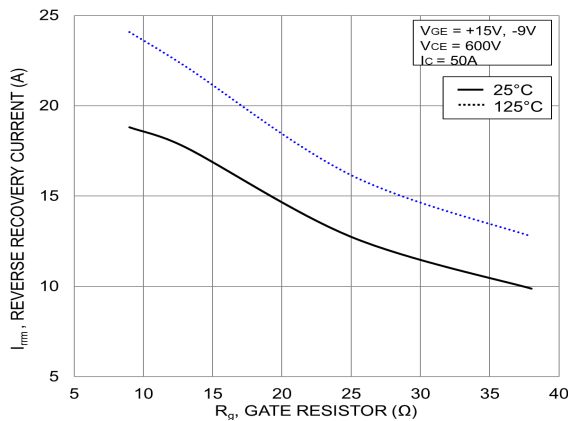


Figure 34. Typical Reverse Recovery Peak Current vs. R_g

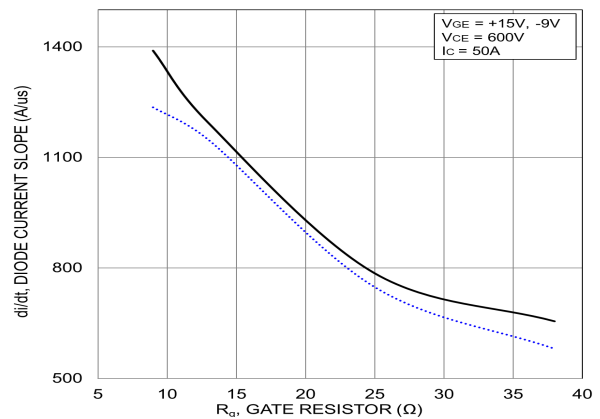
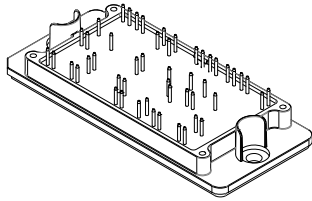


Figure 35. Typical di/dt vs. R_g

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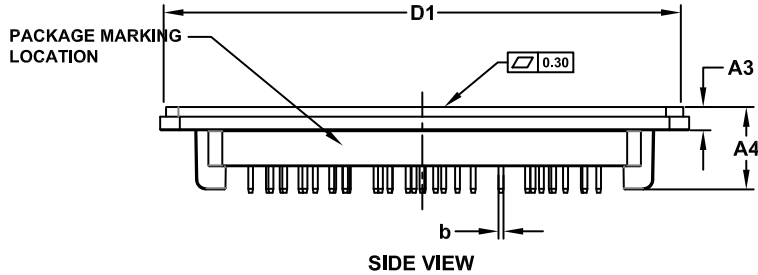
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



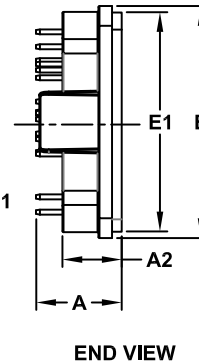
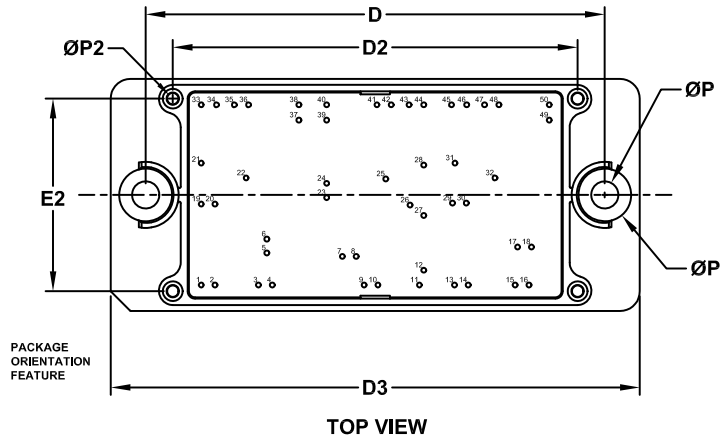
PIM56, 93x47 (SOLDER PIN)
CASE 180BK
ISSUE O

DATE 19 MAY 2022



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009
2. CONTROLLING DIMENSION : MILLIMETERS
3. DIMENSIONS b AND b1 APPLY TO THE PLATED TERMINALS AND ARE MEASURED AT DIMENSION A1
4. PIN POSITION TOLERANCE IS $\pm 0.4\text{mm}$
5. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES



| DIM | MILLIMETERS | | |
|-----|-------------|--------|--------|
| | MIN. | NOM. | MAX. |
| A | 16.80 | 17.20 | 17.60 |
| A2 | 11.70 | 12.00 | 12.30 |
| A3 | 4.40 | 4.70 | 5.00 |
| A4 | 16.40 | 16.70 | 17.00 |
| b | 0.95 | 1.00 | 1.05 |
| D | 92.90 | 93.00 | 93.10 |
| D1 | 104.45 | 104.75 | 105.05 |
| D2 | 81.80 | 82.00 | 82.20 |
| D3 | 106.90 | 107.20 | 107.50 |
| E | 46.70 | 47.00 | 47.30 |
| E1 | 44.10 | 44.40 | 44.70 |
| E2 | 38.80 | 39.00 | 39.20 |
| P | 5.40 | 5.50 | 5.60 |
| P1 | 10.60 | 10.70 | 10.80 |
| P2 | 1.80 | 2.00 | 2.20 |

NOTE 4

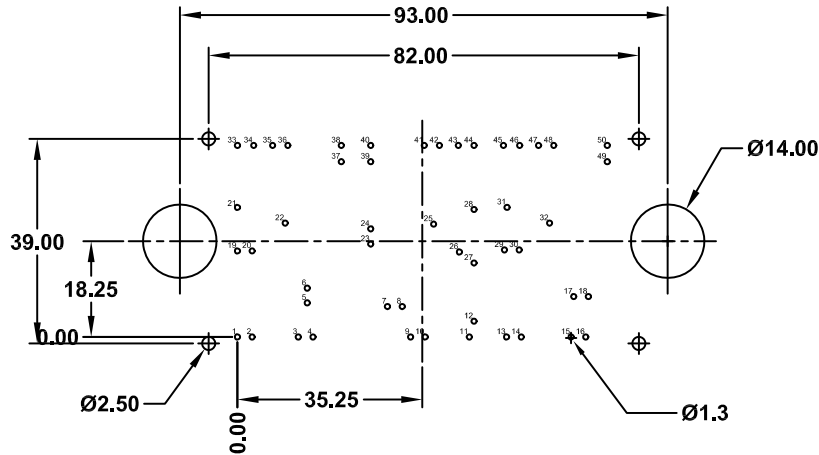
| Pin # | X | Y | Function | Pin # | X | Y | Function |
|-------|------|------|----------|-------|------|------|----------|
| 1 | 0 | 0 | BSC12 | 26 | 42.3 | 16.2 | G21 |
| 2 | 2.8 | 0 | BSC12 | 27 | 45.1 | 14.1 | E21 |
| 3 | 11.6 | 0 | BSC11 | 28 | 45.1 | 24.3 | N2 |
| 4 | 14.4 | 0 | BSC11 | 29 | 50.9 | 16.6 | E31 |
| 5 | 13.3 | 6.5 | BST1 | 30 | 53.7 | 16.6 | G31 |
| 6 | 13.3 | 9.3 | BST1 | 31 | 51.4 | 24.7 | N3 |
| 7 | 28.6 | 5.8 | BST2 | 32 | 59.5 | 21.7 | C32 |
| 8 | 31.4 | 5.8 | BST2 | 33 | 0 | 36.5 | DC-1 |
| 9 | 33 | 0 | BSC21 | 34 | 3.1 | 36.5 | DC-1 |
| 10 | 35.8 | 0 | BSC21 | 35 | 6.7 | 36.5 | E12 |
| 11 | 44.2 | 0 | BSC22 | 36 | 9.6 | 36.5 | G12 |
| 12 | 45.1 | 3 | BSC22 | 37 | 19.8 | 33.4 | DC+1 |
| 13 | 51.3 | 0 | BSC32 | 38 | 19.8 | 36.5 | DC+1 |
| 14 | 54.1 | 0 | BSC32 | 39 | 25.4 | 33.4 | DC+2 |
| 15 | 63.6 | 0 | BSC31 | 40 | 25.4 | 36.5 | DC+2 |
| 16 | 66.4 | 0 | BSC31 | 41 | 35.6 | 36.5 | G22 |
| 17 | 64.1 | 7.7 | BST3 | 42 | 38.5 | 36.5 | E22 |
| 18 | 66.9 | 7.7 | BST3 | 43 | 42.1 | 36.5 | DC-2 |
| 19 | 0 | 16.4 | E11 | 44 | 45.1 | 36.5 | DC-2 |
| 20 | 2.8 | 16.4 | G11 | 45 | 50.7 | 36.5 | DC-3 |
| 21 | 0 | 24.7 | N1 | 46 | 53.8 | 36.5 | DC-3 |
| 22 | 9.1 | 21.7 | C12 | 47 | 57.4 | 36.5 | E32 |
| 23 | 25.4 | 17.7 | TH2 | 48 | 60.3 | 36.5 | G32 |
| 24 | 25.4 | 20.6 | TH1 | 49 | 70.5 | 33.4 | DC+3 |
| 25 | 37.4 | 21.5 | C22 | 50 | 70.5 | 36.5 | DC+3 |

| | | |
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PIM56, 93x47 (SOLDER PIN)
CASE 180BK
ISSUE O

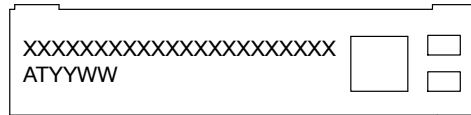
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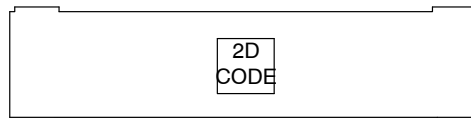
RECOMMENDED MOUNTING PATTERN

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



FRONTSIDE MARKING



BACKSIDE MARKING

XXXXX = Specific Device Code
 AT = Assembly & Test Site Code
 YYWW = Year and Work Week Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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